## DECLARATION FOR NON-PROVISIONAL PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below at 201 et seq. beneath my name.

I believe I am the original, first and sole inventor if only one name is listed at 201 below, or an original, first and joint inventor if plural names are listed at 201 et seq. below, of the subject matter which is claimed and for which a patent is sought on the invention entitled

## METHOD AND APPARATUS FOR ADJUSTING THE THICKNESS OF A LAYER OF SEMICONDUCTOR MATERIAL

and for which a patent application  ✓ is attached hereto and include	on: es amendment(s) filed on		(if a	onlicable)	
was filed in the United States	on as Application N	0.		(declaration not	
accompanying application) v	vith amendment(s) filed on	on		(if applicable)	
was filed as PCT international	l Application No.	on	an	d was amended	
under PCT Article 19 on			(if applicable	)	
amended by any amendment refe	erred to above.	ents of the above identified app	·		
I hereby claim foreign priority b inventor's certificate listed below a filing date before that of the ap	v and have also identified belov	States Code, § 119(a)-(d) of any for any foreign application for pate laimed:	oreign application ent or inventor's	on(s) for patent or certificate having	
EARLIEST FOREIGN APP	LICATION(S), IF ANY, FILE	D PRIOR TO THE FILING DA	TE OF THE AP	PLICATION	
APPLICATION NUMBER	COUNTRY	DATE OF FILING (day, month, year)	PRIORITY CLAIMED		
0210208	France	August 12, 2002	⊠ YES	□ NO	
0210209	France	August 12, 2002	⊠ YES	□ NO	
I hereby claim the benefit unde	er Title 35, United States Code	e, § 119(e) of any United States	s provisional ap	plication(s) listed	
PROVISIONAL APPLICATION NUMBER		FILING DATE			
as the subject matter of each of t provided by the first paragraph of	the claims of this application is of Title 35, United States Code	§ 120 of any United States applic not disclosed in the prior United e § 112, I acknowledge the duty de of Federal Regulations, § 1.56	l States applicati to disclose infor	on in the manner mation known to	

FILING DATE	STATUS			
TIENG DATE	PATENTED	PENDING	ABANDONED	
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	FILING DATE	FILING DATE PATENTED	FILING DATE	

<sup>\*</sup> for use only when the application is assigned to a company, partnership or other organization.

the filing date of the prior application and the national or PCT international filing date of this application:

1.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Application No.:

Group Art Unit:

Filing Date: August 6, 2003

Examiner:

For:

METHOD AND APPARATUS

Attorney Docket No.: 4717-6300

FOR ADJUSTING THE THICKNESS

OF A LAYER OF SEMICONDUCTOR MATERIAL

## POWER OF ATTORNEY BY ASSIGNEE AND EXCLUSION OF INVENTOR(S) UNDER 37 C.F.R. 3.71

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

The undersigned assignee of the entire interest in the above-identified subject application hereby appoints Allan A. Fanucci (Reg. No. 30,256) and Daniel J. Hulseberg (Reg. No. 36,554) of WINSTON & STRAWN (Customer No. 28765) to prosecute this application and to transact all business in the United States Patent and Trademark Office connected therewith.

Please direct all correspondence for this application to Customer No. 28765 to the attention of Allan A. Fanucci (telephone 212-294-3311, facsimile 212-294-4700).

An assignment of the entire interest in the above-identified subject application is submitted herewith for recording and a copy is attached. The undersigned has reviewed this assignment and, to the best of his knowledge, title is in the assignee seeking to take action in this application and that he is empowered to act on its behalf.

Α	S	S	I	G	N	ΙE	E	:

S.O.I. TEC SILICON ON INSULATOR TECHNOLOGIES S.A.

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